

ASMEX.328A



PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Stan
7-18-02

Applicant : Michael A. Todd) Group Art Unit Unknown
Appl. No. : 10/074,633)
Filed : February 11, 2002) I hereby certify that this correspondence and
For : DEPOSITION OVER MIXED) all marked attachments are being deposited
SUBSTRATES (as amended)) with the United States Postal Service as first-
Examiner : Unknown) class mail in an envelope addressed to:
) United States Patent and Trademark Office,
) P.O. Box 2327, Arlington, VA 22202, on
)
) 4/9/02
) (Date)
)
) Joseph J. Mallon
Joseph J. Mallon, Reg. No. 39,287

PRELIMINARY AMENDMENT

United States Patent and Trademark Office
P.O. Box 2327
Arlington, VA 22202

Dear Sir:

Prior to examination, please amend the above-referenced application as follows:

IN THE TITLE:

Please amend the title to read as follows:

DEPOSITION OVER MIXED SUBSTRATES

IN THE ABSTRACT:

Please replace the Abstract with the following new Abstract:

Chemical vapor deposition methods are used to deposit silicon-containing films over mixed substrates. Such methods are useful in semiconductor manufacturing to provide a variety of advantages, including uniform deposition over heterogeneous surfaces, high deposition rates, and higher manufacturing productivity. An example is in forming the base region of a heterojunction bipolar transistor, including simultaneous deposition over both single crystal semiconductor surfaces and amorphous insulating regions.